

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D Max T _A = +25°C |
|-------------------|--------------------------------|--|
| | 73mΩ @ V _{GS} = 10V | 3.3A |
| 30V | 110mΩ @ V _{GS} = 4.5V | 2.7A |

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- General Purpose Interfacing Switch
- Power Management Functions
- **Boost Application**
- Analog Switch

Features and Benefits

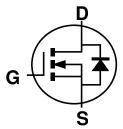
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

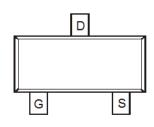
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.027 grams (Approximate)







Equivalent Circuit



Top View

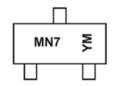
Ordering Information (Note 5)

| - | | |
|-------------|-------|------------------|
| Part Number | Case | Packaging |
| DMN3110SQ-7 | SOT23 | 3000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



MN7 = Product Type Marking Code Y or \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

| Year | 2007 | ~ | 2018 | 2019 | 202 | 0 20 | 21 2 | 022 | 2023 | 2024 | 2025 | 2026 |
|-------|------|-----|------|------|-----|------|------|-----|------|------|------|------|
| Code | J | ~ | F | G | Н | | | J | K | L | М | N |
| | | | | | | | | | | | | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit | |
|--|-----------------|----------------------------------|------------------|------------|---|
| Drain-Source Voltage | | V _{DSS} | 30 | V | |
| Gate-Source Voltage | | | V _{GSS} | ±20 | V |
| Continuous Drain Current (Note 6) V _{GS} = 10V | Steady State | $T_A = +25$ °C $T_A = +70$ °C | I _D | 2.5 2.0 | А |
| Continuous Drain Current (Note 6) V _{GS} = 4.5V | Steady State | $T_A = +25$ °C $T_A = +70$ °C | I _D | 3.3 2.7 | Α |
| Continuous Drain Current (Note 7) V _{GS} = 10V | t≦10sec | $T_A = +25$ °C $T_A = +70$ °C | I _D | 3.8 3.1 | А |
| Continuous Drain Current (Note 7) V _{GS} = 4.5V | Steady State | $T_A = +25$ °C $T_A = +70$ °C | I _D | 2.7 2.1 | А |
| Pulsed Drain Current (Note 8) | | | I _{DM} | 25 | Α |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|--|-----------------|-------------|------|
| Total Power Dissipation (Note 6) | P_{D} | 0.74 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | $R_{	hetaJA}$ | 173.4 | °C/W |
| Total Power Dissipation (Note 7) | P_{D} | 1.3 | W |
| Thermal Resistance, Junction to Ambient (Note 7) | $R_{	hetaJA}$ | 99.1 | °C/W |
| Total Power Dissipation (Note 7) t≦10sec | P_{D} | 1.8 | W |
| Thermal Resistance, Junction to Ambient (Note 7) t≤10sec | $R_{	hetaJA}$ | 72 | °C/W |
| Operating and Storage Temperature Range | $T_{J,}T_{STG}$ | -55 to +150 | °C |

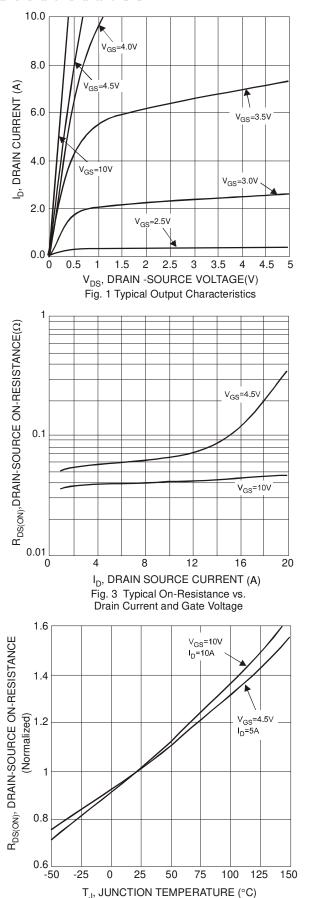
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

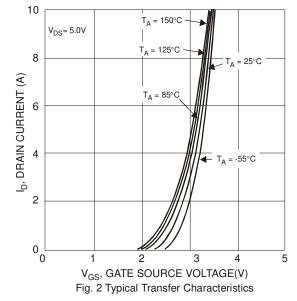
| Characteristic | | Symbol | Min | Тур | Max | Unit | Test Condition |
|---|---------|---------------------|-----|-------|------|-------|--|
| OFF CHARACTERISTICS (Note 9) | • | | | | | | |
| Drain-Source Breakdown Voltage | | BV_{DSS} | 30 | - | - | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| Zero Gate Voltage Drain Current @T _C = | = +25°C | I_{DSS} | - | - | 1.0 | μΑ | $V_{DS} = 30V, V_{GS} = 0V$ |
| Gate-Source Leakage | | I _{GSS} | - | - | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 9) | | | | | | | |
| Gate Threshold Voltage | | $V_{GS(TH)}$ | 1.0 | - | 3.0 | V | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ |
| Static Drain-Source On-Resistance | | | | 54 | 73 | mΩ | $V_{GS} = 10V, I_D = 3.1A$ |
| Static Drain-Source Oil-nesistance | | R _{DS(ON)} | - | 88 | 110 | 11122 | $V_{GS} = 4.5V, I_D = 2A$ |
| Forward Transfer Admittance | | Y _{fs} | - | 4.8 | - | mS | $V_{DS} = 10V, I_D = 3.1A$ |
| Diode Forward Voltage (Note 7) | | V_{SD} | | 0.75 | 1.0 | V | $V_{GS} = 0V, I_{S} = 1A$ |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | |
| Input Capacitance | | Ciss | - | 305.8 | - | рF | \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ |
| Output Capacitance | | Coss | - | 39.9 | - | pF | $V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz |
| Reverse Transfer Capacitance | | C_{rss} | - | 39.5 | - | рF | 1 = 1:001112 |
| Gate Resistance | | R_g | | 1.4 | - | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$ |
| Total Gate Charge (V _{GS} = 4.5V) | | Qg | - | 4.1 | - | nC | |
| Total Gate Charge (V _{GS} = 10V) | | Q_g | | 8.6 | - | nC | V 10V I 2A |
| Gate-Source Charge | | Q _{gs} | - | 1.2 | - | nC | $V_{DS} = 10V, I_{D} = 3A$ |
| Gate-Drain Charge | | Q _{gd} | - | 1.5 | - | nC | |
| Turn-On Delay Time | | t _{D(ON)} | - | 2.6 | - | ns | |
| Turn-On Rise Time | | t _R | - | 4.6 | - | ns | $V_{DD} = 15V, V_{GS} = 10V,$ |
| Turn-Off Delay Time | | t _{D(OFF)} | - | 13.1 | - | ns | $R_L = 47\Omega$, $R_G = 3\Omega$ |
| Turn-Off Fall Time | | t _F | _ | 2.5 | - | ns | 1 |

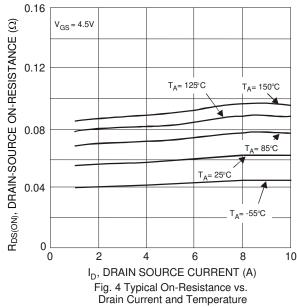
Notes:

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, on 1 inch square copper plate.
 8. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.









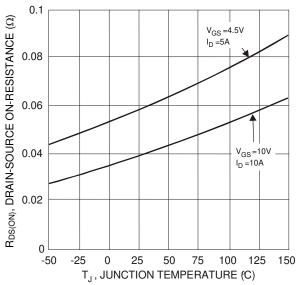


Fig. 5 On-Resistance Variation with Temperature

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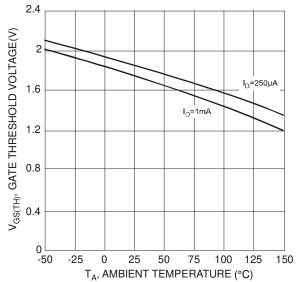
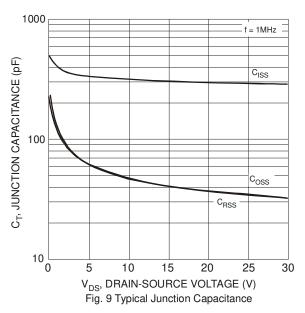
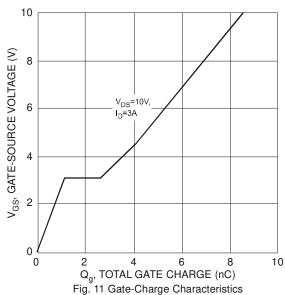
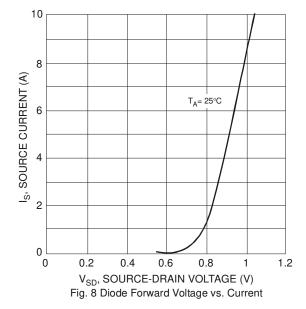
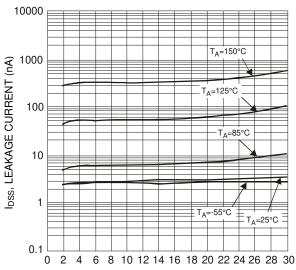


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



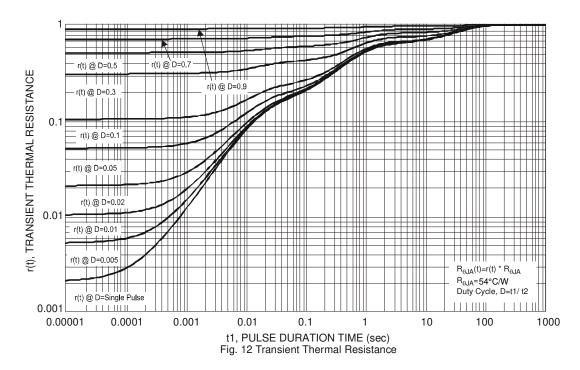






 $\label{eq:VDS} V_{DS}, \, \text{DRAIN-SOURCE VOLTAGE(V)}$ Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

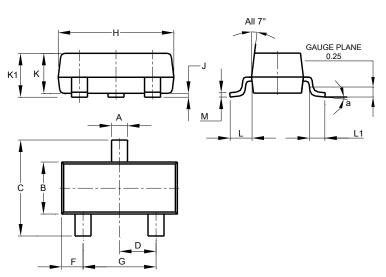




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



| SOT23 | | | | | | | | | |
|----------------------|-------|-------|-------|--|--|--|--|--|--|
| Dim | Min | Max | Тур | | | | | | |
| Α | 0.37 | 0.51 | 0.40 | | | | | | |
| В | 1.20 | 1.40 | 1.30 | | | | | | |
| С | 2.30 | 2.50 | 2.40 | | | | | | |
| D | 0.89 | 1.03 | 0.915 | | | | | | |
| F | 0.45 | 0.60 | 0.535 | | | | | | |
| G | 1.78 | 2.05 | 1.83 | | | | | | |
| Н | 2.80 | 3.00 | 2.90 | | | | | | |
| J | 0.013 | 0.10 | 0.05 | | | | | | |
| K | 0.890 | 1.00 | 0.975 | | | | | | |
| K1 | 0.903 | 1.10 | 1.025 | | | | | | |
| L | 0.45 | 0.61 | 0.55 | | | | | | |
| L1 | 0.25 | 0.55 | 0.40 | | | | | | |
| М | 0.085 | 0.150 | 0.110 | | | | | | |
| а | 0° | 8° | | | | | | | |
| All Dimensions in mm | | | | | | | | | |

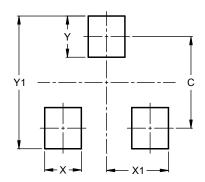
May 2019



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 2.0 |
| Х | 0.8 |
| X1 | 1.35 |
| Υ | 0.9 |
| Y1 | 2.9 |

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